WE CLAIM AS OUR INVENTION:

1) A microsampling device comprising:

a substrate defining a microsampler chamber; and

a cuvette window formed of silicon nitride.

2) The device of Claim 1 wherein the substrate is silicon.

3) The device of Claim 2 wherein the silicon substrate has a thickness of approximately 500 micrometers.

4) The device of Claim 1 wherein the silicon nitride window has a thickness of approximately 0.01 to 5 micrometers.

5) The device of Claim 1 wherein the chamber has a volume of less than 1 micrometer.

6) A method of constructing a cuvette window in the microsampler chamber of a microsampling device, the method comprising

providing a silicon wafer having a top surface and a bottom surface;

etching a patterned depression in the top surface of the silicon wafer thereby defining the microsampler chamber;

depositing a silicon nitride film on the top surface of the silicon wafer; and

etching a patterned depression in the bottom surface of the silicon wafer and exposing the silicon nitride film forming the window.

7) The method of Claim 6 wherein the silicon wafer has a thickness of approximately 500 micrometers.

8) The method of Claim 6 wherein the silicon nitride film has a thickness of approximately 0.01 to 5 micrometers.

9) A silicon device comprising:

a silicon substrate defining a cuvette; and

a cuvette window formed of silicon nitride.

10) The device of Claim 9 wherein the silicon nitride window has a thickness of approximately 0.01 to 5 micrometers.

11)A method of constructing a window in the cuvette of a silicon device, the method comprising

providing a silicon substrate having a top surface and a bottom surface;

etching a patterned depression in the top surface of the silicon wafer thereby defining the cuvette;

depositing a silicon nitride film on the top surface of the silicon wafer; and

etching a patterned depression in the bottom surface of the silicon wafer and exposing the silicon nitride film forming the window.

12)The method of Claim 12 wherein the substrate is a silicon wafer.

13)The method of Claim 12 wherein the silicon nitride film has a thickness of approximately 0.01 to 5 micrometers.